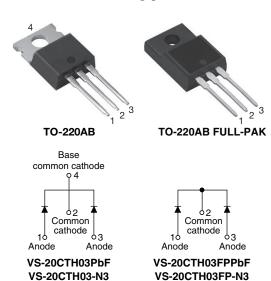


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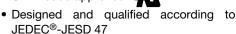
Hyperfast Rectifier, 2 x 10 A FRED Pt®



PRODUCT SUMMARY						
Package	TO-220AB, TO-220FP					
I _{F(AV)}	2 x 10 A					
V_{R}	300 V					
V _F at I _F	0.85 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- · Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 approved



 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

DESCRIPTION / APPLICATIONS

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS V					
Peak repetitive reverse voltage		V_{RRM}			300				
Average rectified forward current	per diode	I _{F(AV)}	T _C = 160 °C	10					
	(FULL-PAK) per diode		T _C = 135 °C						
	per device			20	А				
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C	120					
Operating junction and storage temperatures		T _J , T _{Stg}		-65 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	300	-	-		
Forward voltage	V _E	I _F = 10 A	-	1.05	1.25	V	
	VF	I _F = 10 A, T _J = 125 °C	-	0.85	0.95		
Poverse leekage current		V _R = V _R rated	-	-	20		
Reverse leakage current	I _R	$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	6	200	μA	
Junction capacitance	C _T	V _R = 300 V	-	30	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	



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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A}$	/μs, V _R = 30 V	-	-	35		
	+	$I_F = 1 \text{ A, } dI_F/dt = 100 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$		-	-	30		
	t _{rr}	T _J = 25 °C	$I_F = 10 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	31	-	ns	
		T _J = 125 °C		-	42	-		
Dook roopyon/ ourrent	I _{RRM}	T _J = 25 °C		-	2.4	-	Α	
Peak recovery current		T _J = 125 °C		-	5.6	-		
Reverse recovery charge		T _J = 25 °C		-	36	-	200	
	Q_{rr}	T _J = 125 °C		-	120	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance,	per diode		Mounting surface, flat, smooth, and greased	-	-	1.5	°C/W	
junction to case	(FULL-PAK) per diode	R_{thJC}		-	-	3.9	C/VV	
Marking device			Case style TO-220AB	20CTH03				
		Case style TO-220 FULL-PAK		20CTH03FP				

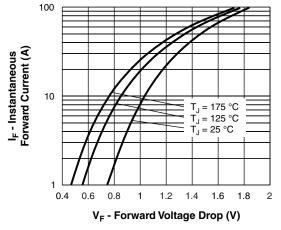


Fig. 1 - Typical Forward Voltage Drop Characteristics

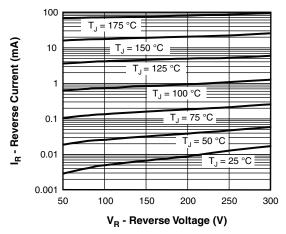


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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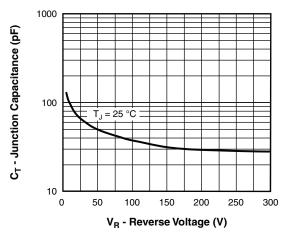


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

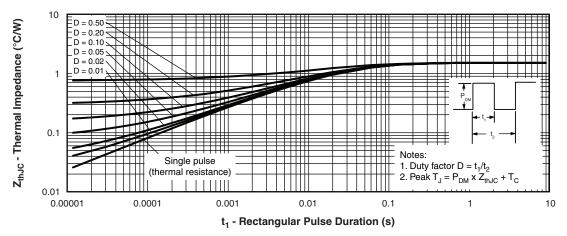


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

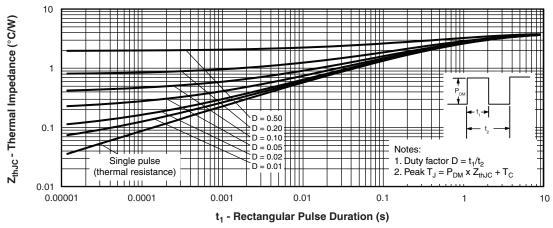


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

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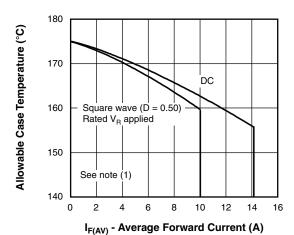


Fig. 6 - Maximum Allowable Case Temperature vs.
Average Forward Current

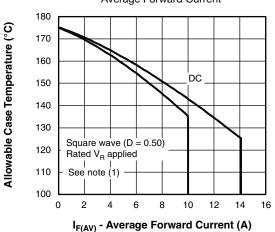


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

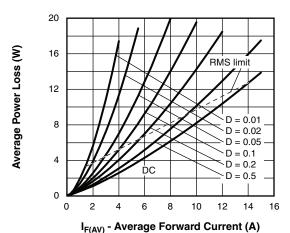


Fig. 8 - Forward Power Loss Characteristics

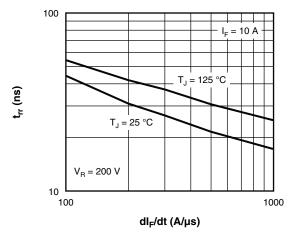


Fig. 9 - Typical Reverse Recovery Time vs. dl_F/dt

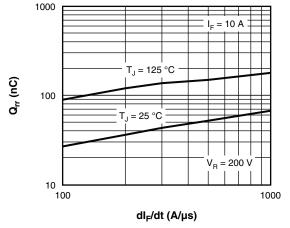


Fig. 10 - Typical Stored Charge vs. dl_F/dt

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = forward power loss = I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 8); $Pd_{REV} = inverse power loss = V_{B1} \times I_B$ (1 - D); I_B at $V_{B1} = rated V_B$

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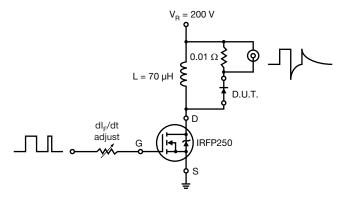
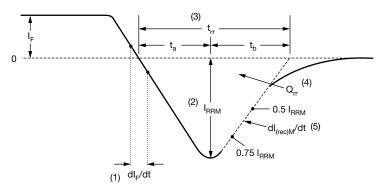


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

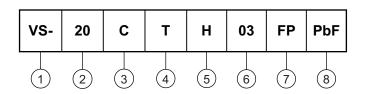
(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 12 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (20 = 20 A)

C = common cathode

T = TO-220, D²PAK

5 - H = hyperfast recovery

- Voltage rating (03 = 300 V)

7 - • None = TO-220AB

• FP = TO-220 FULL-PAK

8 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

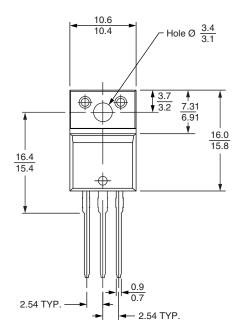
-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

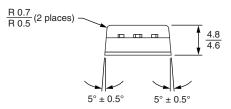
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-20CTH03PbF	50	1000	Antistatic plastic tube				
VS-20CTH03-N3	50	1000	Antistatic plastic tube				
VS-20CTH03FPPbF	50	1000	Antistatic plastic tube				
VS-20CTH03FP-N3	50	1000	Antistatic plastic tube				

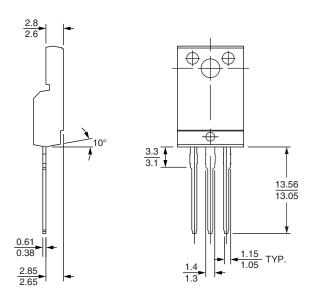
LINKS TO RELATED DOCUMENTS						
Dimensions	TO-220AB	www.vishay.com/doc?95222				
Differisions	TO-220FP	www.vishay.com/doc?95072				
	TO-220ABPbF	www.vishay.com/doc?95225				
Dort marking information	TO-220AB-N3	www.vishay.com/doc?95028				
Part marking information	TO-220FPPbF	www.vishay.com/doc?95069				
	TO-220FP-N3	www.vishay.com/doc?95456				

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DIMENSIONS in millimeters







Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

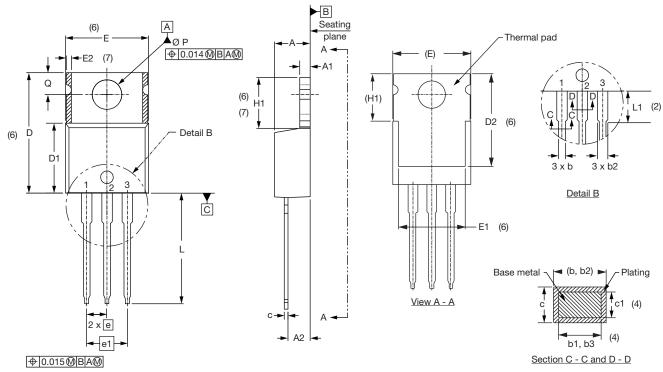
Conforms to JEDEC outline TO-220 FULL-PAK



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TO-220AB

DIMENSIONS in millimeters and inches



Lead tip

Lead assignments

<u>Diodes</u>

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	MILLIMETERS		INCHES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° t	o 93°	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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